## **EAST Search History**

| Ref<br># | Hits  | Search Query  | DBs   | Default<br>Operator | Plurals | Time Stamp       |
|----------|-------|---|---|---------------------|---------|------------------|
| L4       | 16580 | ((local\$2 or selective\$2) same<br>etch\$3) same (silicon near oxide or<br>"SiO.sub.2")                            | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR                  | OFF     | 2006/04/21 08:48 |
| L5       | 8     | L4 same (spray\$3 same gas\$3)  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR                  | OFF     | 2006/04/21 08:48 |
| L6       | 1     | yanagisawa-michihiko.in. and (local\$2 same etch\$3) same (silicon near oxide or "SiO.sub.2")                       | US-PGPUB;<br>USPAT                                      | OR                  | OFF     | 2006/04/21 08:54 |
| L7       | 32    | yanagisawa-michihiko.in.  | US-PGPUB;<br>USPAT                                      | OR                  | OFF     | 2006/04/21 09:01 |
| L8       | 14182 | ((dry or plasma) near etch\$3 and silicon and silicon near oxide and nozzle or eject\$3 and control\$4). clm.       | US-PGPUB;<br>USPAT                                      | OR                  | OFF     | 2006/04/21 09:03 |
| L9       | 14    | (((dry or plasma) near etch\$3) and silicon and (silicon near oxide) and (nozzle or eject\$3) and control\$4). clm. | US-PGPUB;<br>USPAT                                      | OR                  | OFF     | 2006/04/21 09:04 |

## **EAST Search History**

| Def      |      | Carriel Outre  | 00  | D.C. B              | Diam - I | T C:             |
|----------|------|--|---|---------------------|----------|------------------|
| Ref<br># | Hits | Search Query   | DBs   | Default<br>Operator | Plurals  | Time Stamp       |
| L1       | 40   | ( etch\$3 same (silicon near oxide or "SiO.sub.2")) same (eject\$3 or nozzle)  | EPO; JPO;<br>DERWENT;<br>IBM_TDB                        | OR                  | OFF      | 2006/04/21 13:18 |
| L2       | 670  | (etch\$3 same silicon) same (eject\$3 or jet\$4 or nozzle)                     | EPO; JPO;<br>DERWENT;<br>IBM_TDB                        | OR                  | OFF      | 2006/04/21 13:19 |
| L3       | 107  | (etch\$3 same silicon) same<br>((eject\$3 or jet\$4 or nozzle) same<br>gas\$3) | EPO; JPO;<br>DERWENT;<br>IBM_TDB                        | OR                  | OFF      | 2006/04/21 13:29 |
| L4       | 9    | 3 and (remov\$3 same oxide)  | EPO; JPO;<br>DERWENT;<br>IBM_TDB                        | OR                  | OFF      | 2006/04/21 13:29 |
| L5       | 15   | 3 and ((remov\$3 or etch\$3 or pattern\$3) same oxide)                         | EPO; JPO;<br>DERWENT;<br>IBM_TDB                        | OR                  | OFF      | 2006/04/21 13:28 |
| L6       | 15   | 3 and ((remov\$3 or etch\$3 or pattern\$3) same oxide)                         | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR                  | OFF      | 2006/04/21 13:28 |
| L7       | 552  | (etch\$3 same silicon) same<br>((eject\$3 or jet\$4 or nozzle) same<br>gas\$3) | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR                  | OFF      | 2006/04/21 13:29 |
| L8       | 9    | 7 and (remov\$3 same oxide)  | EPO; JPO;<br>DERWENT;<br>IBM_TDB                        | OR                  | OFF      | 2006/04/21 13:29 |